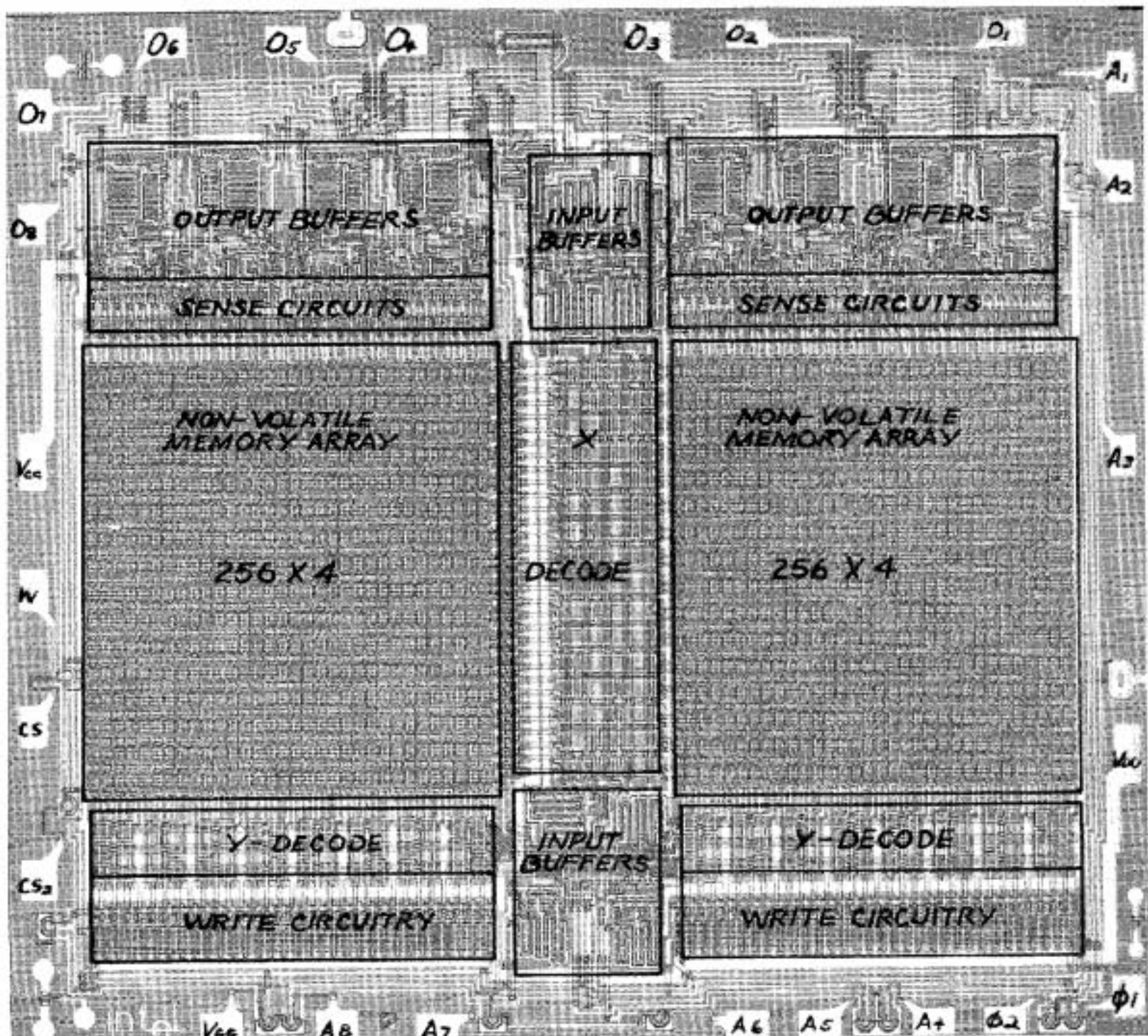# First FAMOS EPROM

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A Fully-Decoded 2048-Bit Electrically-Programmable MOS-ROM

FROHMANN-BENTCHKOWSKY (Intel) presented a 2048 bit FAMOS EPROM. This was the start of ultra violate (UV) EPROM product family, which dominated the non-volatile memory field from mid 1970s to early 1990s. This device achieved non-volatility by charge storage on a floating gate of a p-channel device. The charge was transported to the floating gate by the Avalanche injection, and the charge removal from the floating gate was accomplished by shining UV light.

D. Frohmann-Bentchkowsky
Intel Corp., Mountain View, CA